# The RF Line UHF Linear Power Transistor

The TP3024B is a balanced transistor designed specifically for use in cellular radio systems. This device permits the design of a Class AB push–pull, high gain, broadband amplifier having a high degree of linearity without the need for complicated biasing circuitry.

- Specified 26 Volts, 960 MHz Characteristics: Output Power = 35.5 W Minimum Gain = 7.5 dB IQ<sub>total</sub> = 150 mA
- Push–Pull Configuration



35.5 W, 960 MHz UHF LINEAR POWER TRANSISTOR

CASE 395B-01, STYLE 1

# MAXIMUM RATINGS

Rating	Symbol Value		Unit
Emitter-Base Voltage	V <sub>EBO</sub>	4.0	Vdc
Operating Junction Temperature	ТJ	200	°C
Storage Temperature Range	T <sub>stg</sub>	-65 to +200	°C

# THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case (1) (T <sub>C</sub> = 75°C)	R <sub>θJC</sub>	3.0	°C/W

### **ELECTRICAL CHARACTERISTICS** ( $T_C = 25^{\circ}C$ unless otherwise noted.)

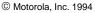
Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage (I <sub>C</sub> = 10 mA, R <sub>BE</sub> = 75 Ohms)	V(BR)CER	40	_	_	Vdc
Collector–Emitter Leakage (V <sub>CE</sub> = 26 V, R <sub>BE</sub> = 75 Ohms)	ICER	_	_	5.0	mA
Emitter–Base Breakdown Voltage ( $I_C = 5.0 \text{ mAdc}, I_C = 0$ )	V <sub>(BR)EBO</sub>	3.5	_	_	Vdc
Emitter-Base Leakage (V <sub>BE</sub> = 2.5 V)	IEBO	—	_	1.0	mA
ON CHARACTERISTICS (2)					
DC Current Gain (I <sub>C</sub> = 500 mA, $V_{CE}$ = 10 V)	hFE	15	_	100	—
DYNAMIC CHARACTERISTICS (1)					
Output Capacitance ( $V_{CB}$ = 24 V, I <sub>E</sub> = 0, f = 1.0 MHz)	C <sub>ob</sub>	—	17	25	pF
FUNCTIONAL TESTS (3)					
Common–Emitter Amplifier Power Gain (V <sub>CE</sub> = 26 V, P <sub>out</sub> = 35.5 W, f = 960 MHz, <sup>I</sup> Q <sub>total</sub> = 150 mA)	GPE	7.5	—	—	dB
Collector Efficiency (V <sub>CE</sub> = 26 V, P <sub>out</sub> = 35.5 W, f = 960 MHz, <sup>I</sup> Q <sub>total</sub> = 150 mA)	η <sub>C</sub>	45	_	_	%

NOTE:

1. Thermal resistance is determined under specified RF operating condition.

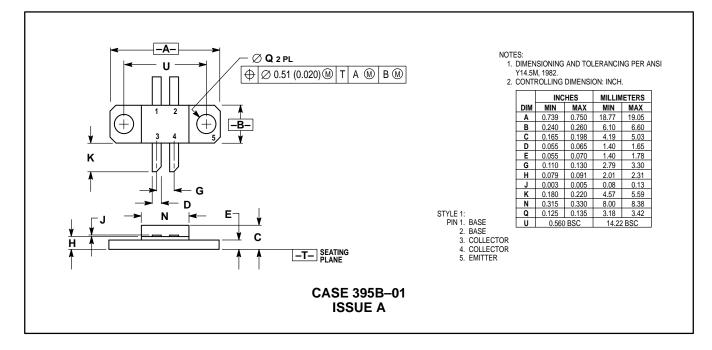
2. Each transistor chip measured separately.

3. Both transistor chips operating in push-pull amplifier.





# PACKAGE DIMENSIONS



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